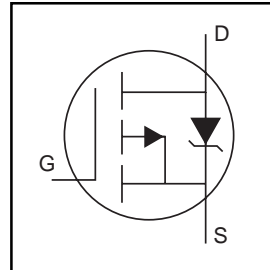


- Advanced Process Technology
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- P-Channel
- Fast Switching
- Fully Avalanche Rated

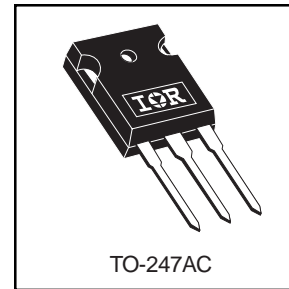


$V_{DSS} = -100V$
$R_{DS(on)} = 0.117\Omega$
$I_D = -23A$

**Description**

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The TO-247 package is preferred for commercial-industrial applications where higher power levels preclude the use of TO-220 devices. The TO-247 is similar but superior to the earlier TO-218 package because of its isolated mounting hole.



**Absolute Maximum Ratings**

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	-23	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	-16	
$I_{DM}$	Pulsed Drain Current ①⑤	-76	
$P_D @ T_C = 25^\circ C$	Power Dissipation	140	W
	Linear Derating Factor	0.91	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$E_{AS}$	Single Pulse Avalanche Energy②⑤	430	mJ
$I_{AR}$	Avalanche Current①	-11	A
$E_{AR}$	Repetitive Avalanche Energy①	14	mJ
dv/dt	Peak Diode Recovery dv/dt ③⑤	-5.0	V/ns
$T_J$	Operating Junction and	-55 to + 175	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

**Thermal Resistance**

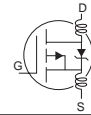
	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	1.1	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.24	—	
$R_{\theta JA}$	Junction-to-Ambient	—	40	

# IRFP9140N

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## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
	$V_{(BR)DSS}$	-100	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
	$\Delta V_{(BR)DSS}/\Delta T_J$	—	-0.11	—	V/°C	Reference to $25^\circ\text{C}, I_D = -1\text{mA}$ ⑤
	$R_{DS(on)}$	—	—	0.117	$\Omega$	$V_{GS} = -10V, I_D = -13A$ ④
	$V_{GS(th)}$	-2.0	—	-4.0	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
	$g_{fs}$	5.3	—	—	S	$V_{DS} = -50V, I_D = 11A$ ⑤
	$I_{DSS}$	—	—	-25	$\mu A$	$V_{DS} = -100V, V_{GS} = 0V$
		—	—	-250		$V_{DS} = -80V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
	$I_{GSS}$	—	—	100	nA	$V_{GS} = 20V$
		—	—	-100		$V_{GS} = -20V$
	$Q_g$	—	—	97	nC	$I_D = -11A$
	$Q_{gs}$	—	—	15		$V_{DS} = -80V$
	$Q_{gd}$	—	—	51		$V_{GS} = -10V$ , See Fig. 6 and 13 ④⑤
	$t_{d(on)}$	—	15	—	ns	$V_{DD} = -50V$ $I_D = -11A$ $R_G = 5.1\Omega$ $R_D = 4.2\Omega$ , See Fig. 10 ④⑤
	$t_r$	—	67	—		
	$t_{d(off)}$	—	51	—		
	$t_f$	—	51	—		
	$L_D$	—	5.0	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
	$L_S$	—	13	—		
	$C_{iss}$	—	1300	—	pF	$V_{GS} = 0V$ $V_{DS} = -25V$ $f = 1.0\text{MHz}$ , See Fig. 5 ⑤
	$C_{oss}$	—	400	—		
	$C_{rss}$	—	240	—		



## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
	$I_S$	—	—	-23	A	MOSFET symbol showing the integral reverse p-n junction diode.
	$I_{SM}$	—	—	-76		
	$V_{SD}$	—	—	-1.3	V	$T_J = 25^\circ\text{C}, I_S = -13A, V_{GS} = 0V$ ④
	$t_{rr}$	—	150	220	ns	$T_J = 25^\circ\text{C}, I_F = -11A$
	$Q_{rr}$	—	830	1200	$\mu C$	$di/dt = -100A/\mu s$ ④
	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$ )				

### Notes:

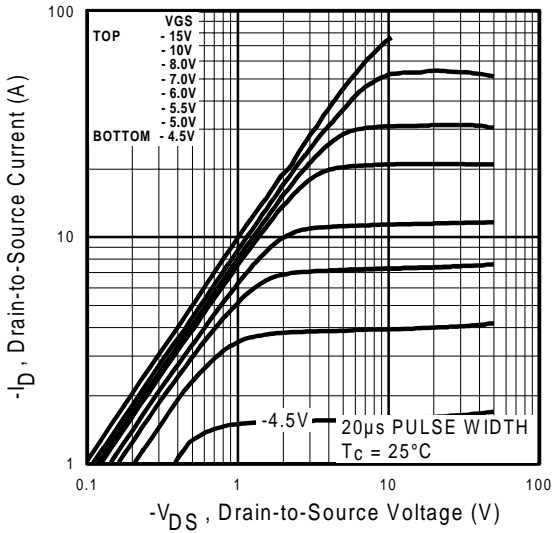
① Repetitive rating; pulse width limited by max. junction temperature. ( See fig. 11 )

② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 7.1\text{mH}$   
 $R_G = 25\Omega, I_{AS} = -11A$ . (See Figure 12)

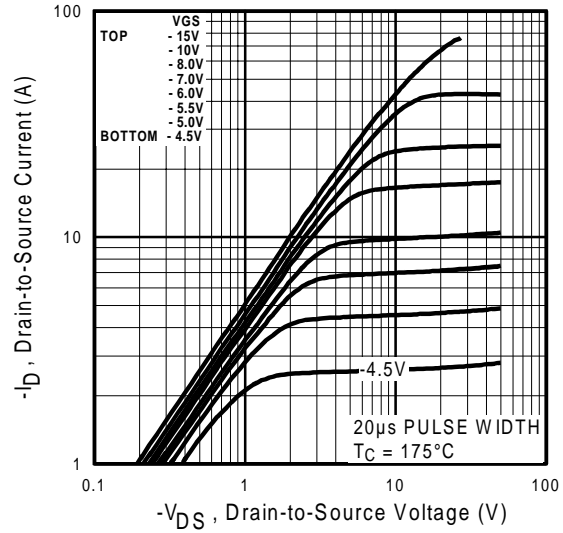
③  $I_{SD} \leq -11A, di/dt \leq -470A/\mu s, V_{DD} \leq V_{(BR)DSS}$   
 $T_J \leq 175^\circ\text{C}$

④ Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$ .

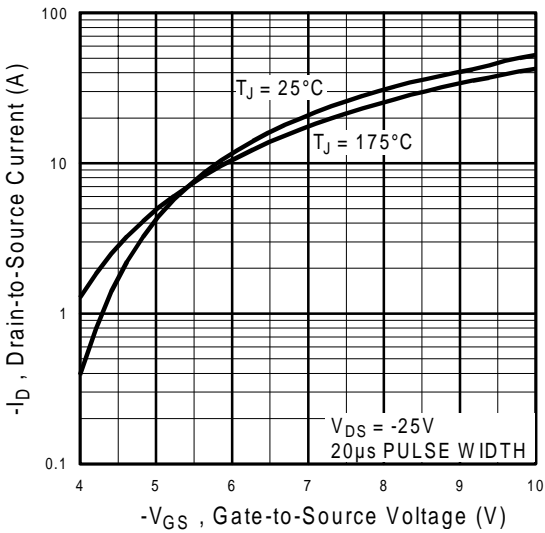
⑤ Uses IRF9540N data and test conditions



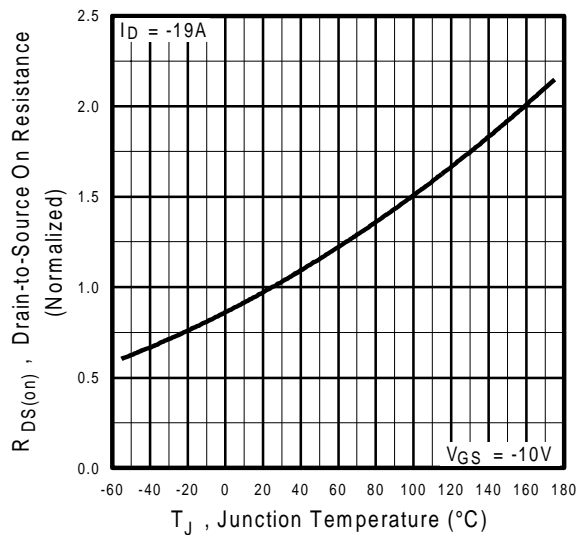
**Fig 1.** Typical Output Characteristics



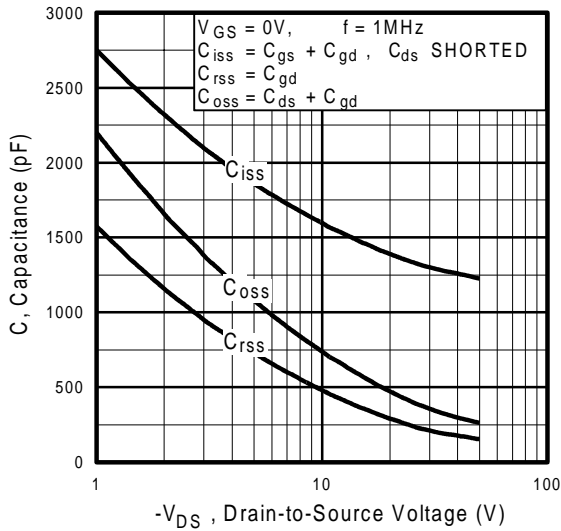
**Fig 2.** Typical Output Characteristics



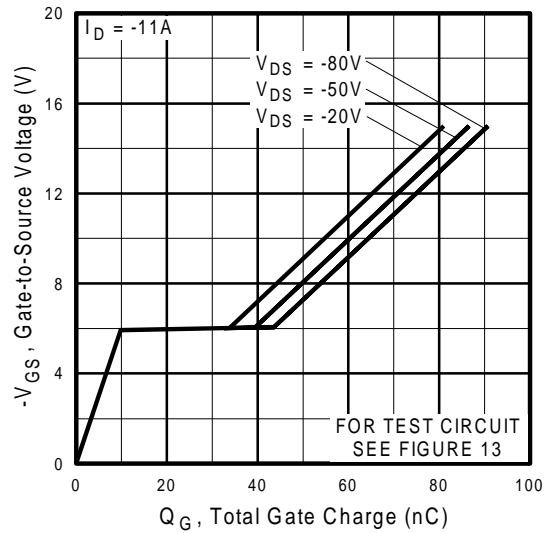
**Fig 3.** Typical Transfer Characteristics



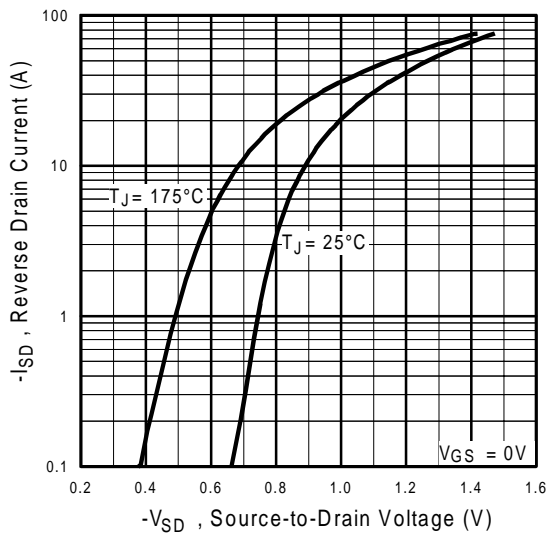
**Fig 4.** Normalized On-Resistance Vs. Temperature



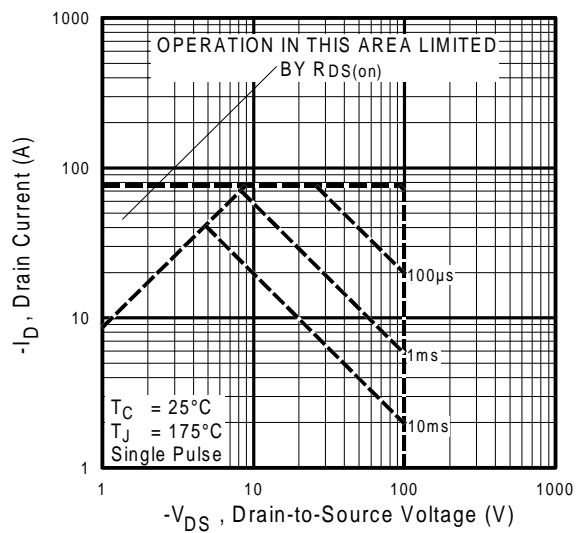
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



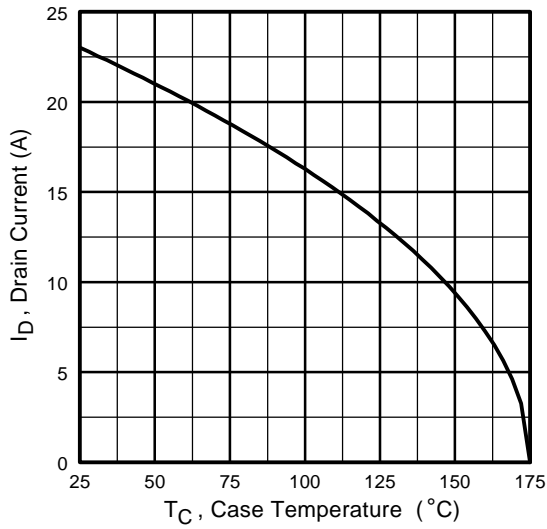
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



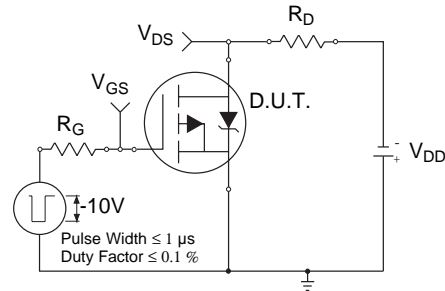
**Fig 7.** Typical Source-Drain Diode Forward Voltage



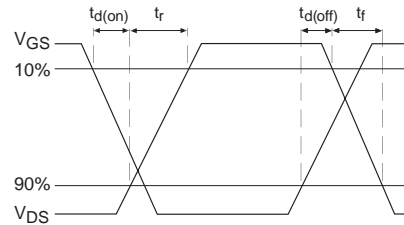
**Fig 8.** Maximum Safe Operating Area



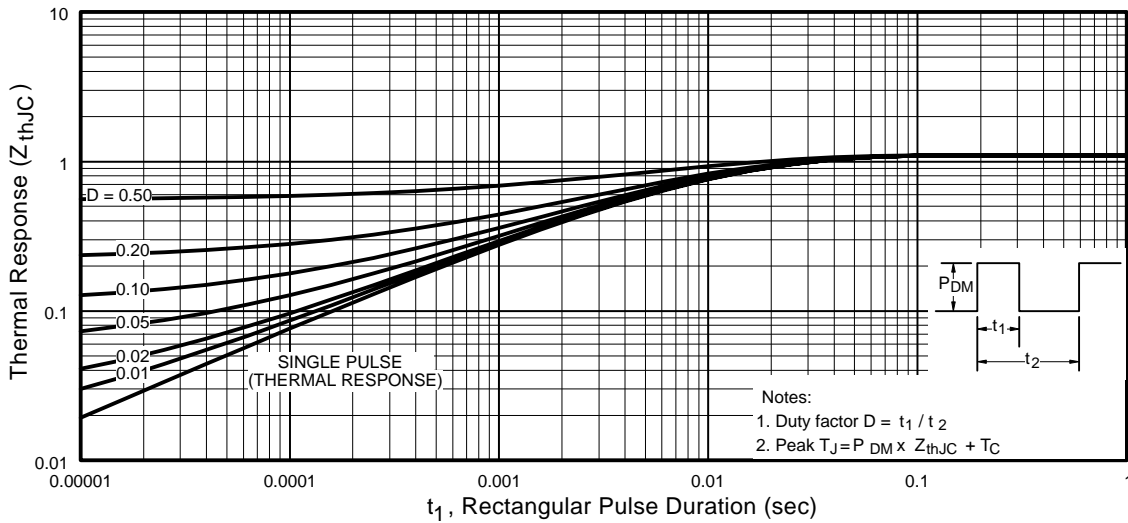
**Fig 9.** Maximum Drain Current Vs. Case Temperature



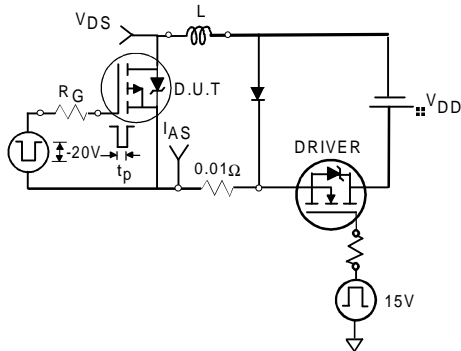
**Fig 10a.** Switching Time Test Circuit



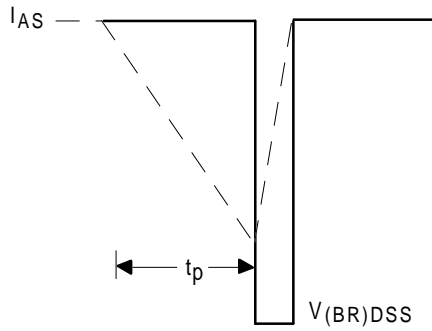
**Fig 10b.** Switching Time Waveforms



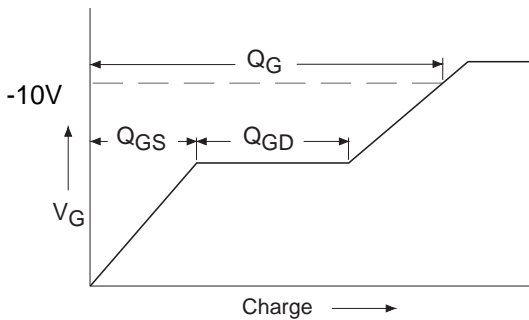
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case



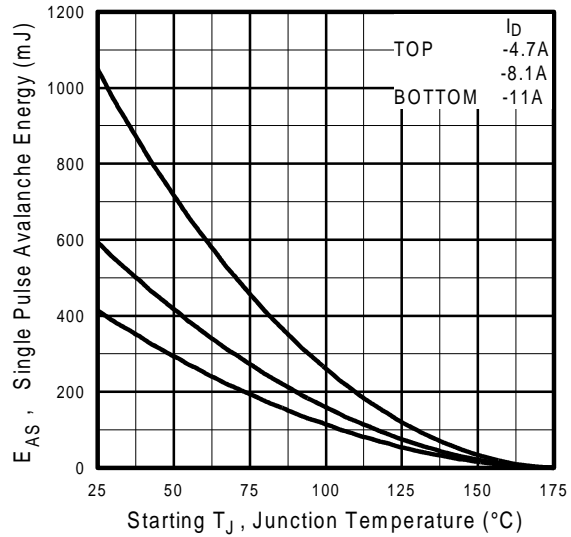
**Fig 12a.** Unclamped Inductive Test Circuit



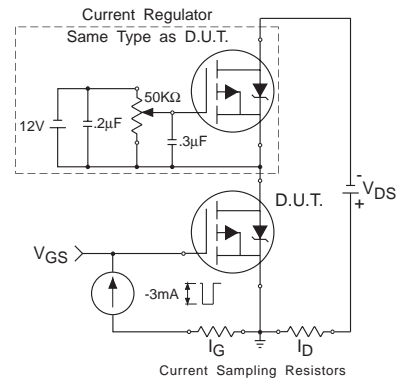
**Fig 12b.** Unclamped Inductive Waveforms



**Fig 13a.** Basic Gate Charge Waveform

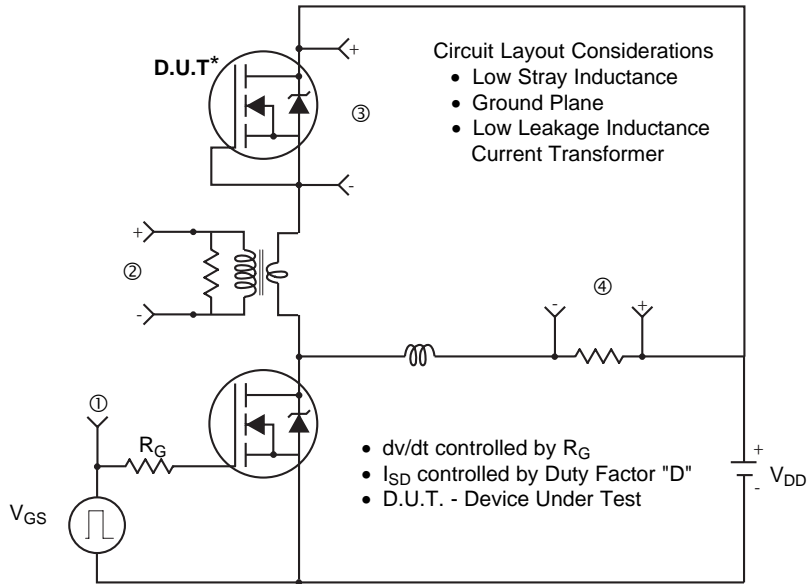


**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current

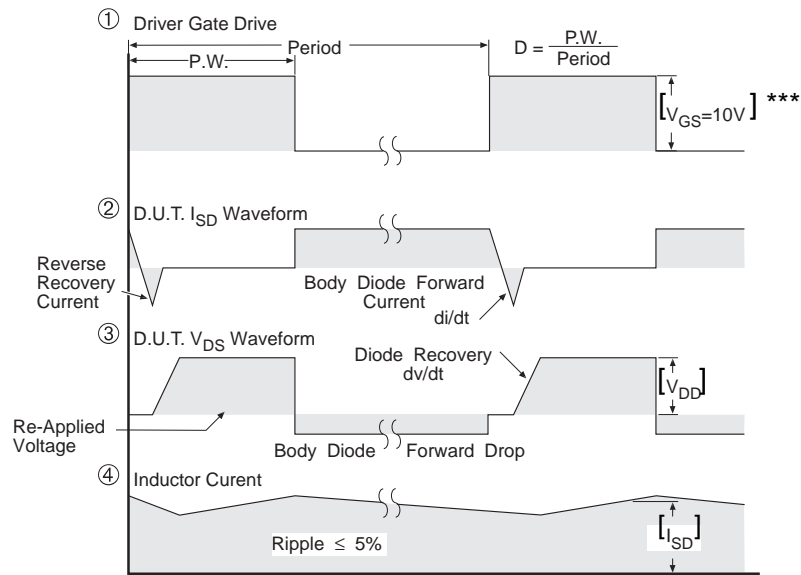


**Fig 13b.** Gate Charge Test Circuit

## Peak Diode Recovery dv/dt Test Circuit



\* Reverse Polarity of D.U.T for P-Channel



\*\*\*  $V_{GS} = 5.0V$  for Logic Level and 3V Drive Devices

**Fig 14.** For P-Channel HEXFETS

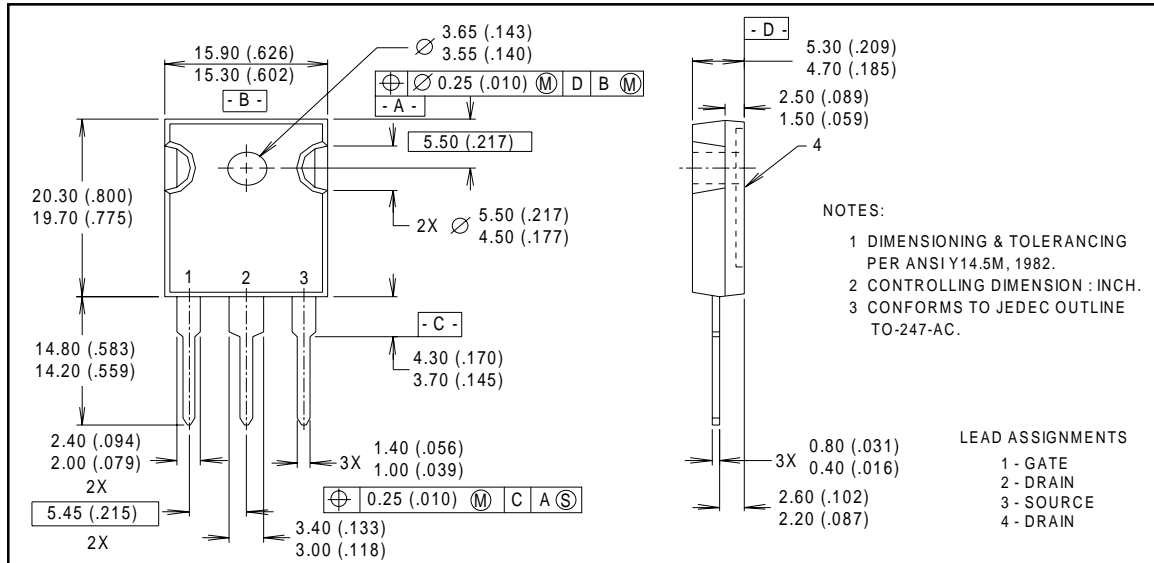
# IRFP9140N

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**IR** Rectifier

## Package Outline

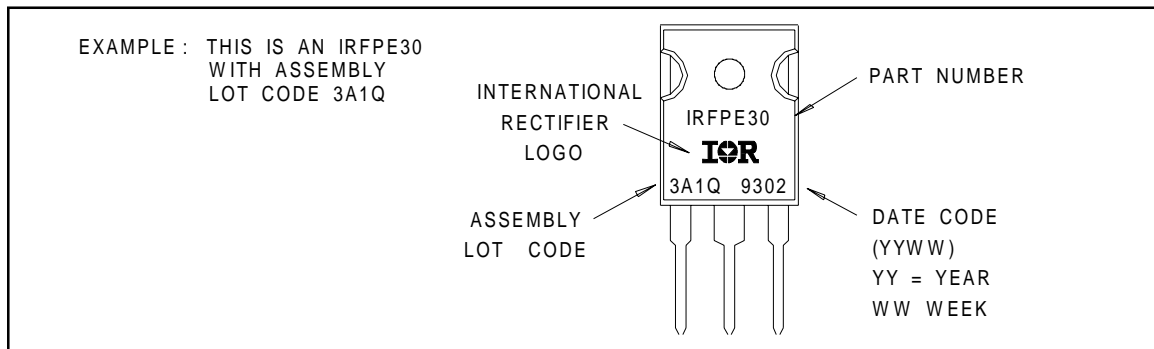
### TO-247AC Outline

Dimensions are shown in millimeters (inches)



## Part Marking Information

### TO-247AC



International  
**IR** Rectifier

**WORLD HEADQUARTERS:** 233 Kansas St., El Segundo, California 90245, Tel: (310) 322 3331  
**EUROPEAN HEADQUARTERS:** Hurst Green, Oxted, Surrey RH8 9BB, UK Tel: ++ 44 1883 732020  
**IR CANADA:** 7321 Victoria Park Ave., Suite 201, Markham, Ontario L3R 2Z8, Tel: (905) 475 1897  
**IR GERMANY:** Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 6172 96590

**IR ITALY:** Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 11 451 0111

**IR FAR EAST:** K&H Bldg., 2F, 3-30-4 Nishi-Ikeburo 3-Chome, Toshima-Ki, Tokyo Japan 171 Tel: 81 3 3983 0086

**IR SOUTHEAST ASIA:** 315 Outram Road, #10-02 Tan Boon Liat Building, Singapore 0316 Tel: 65 221 8371

<http://www.irf.com/>

Data and specifications subject to change without notice.

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